

## GSE C200 PLASMA ETCHER

### System Overview

GSE C200 is an ICP general etcher for silicon and III-V materials, designed with ultra-high density plasma sources for higher etch rates. In addition, the GSE C200 can delayer a wide variety of layers on substrates / chips up to 8" in diameter to conduct a thorough failure analysis on low yield wafers and devices.

<b>Substrate Size:</b>	50 mm, 100 mm, 150 mm, 200 mm Down to wafer pieces for failure analysis
<b>Applications compounds:</b>	Si, Dielectric, Polymer, III-V, and more
<b>Technology Markets:</b>	Power IC, LED, Failure Analysis, and R&D

### Processes

- Passivation etch
- Poly etch
- Nitride etch
- Power GaN devices
- GaAs VCSEL device mesa etching
- GaAs HBT/pHEMT mesa and back hole etching
- InP grating and waveguide etching
- Failure analysis

### Production Advantages

- Process module design optimizes plasma uniformity
- Process chamber design improves maintainability
- Customizable high-precision bias RF—precisely control DC Bias to achieve low-speed, low-damage etching of GaN and other materials
- Lower electrode heating: 20° ~ 180°C, to meet III-V etching requirements
- Automatic matching radio frequency system to achieve fast, effective and accurate matching to ensure process repeatability



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